

**isc Silicon NPN Power Transistor**

**2SC4796**

**DESCRIPTION**

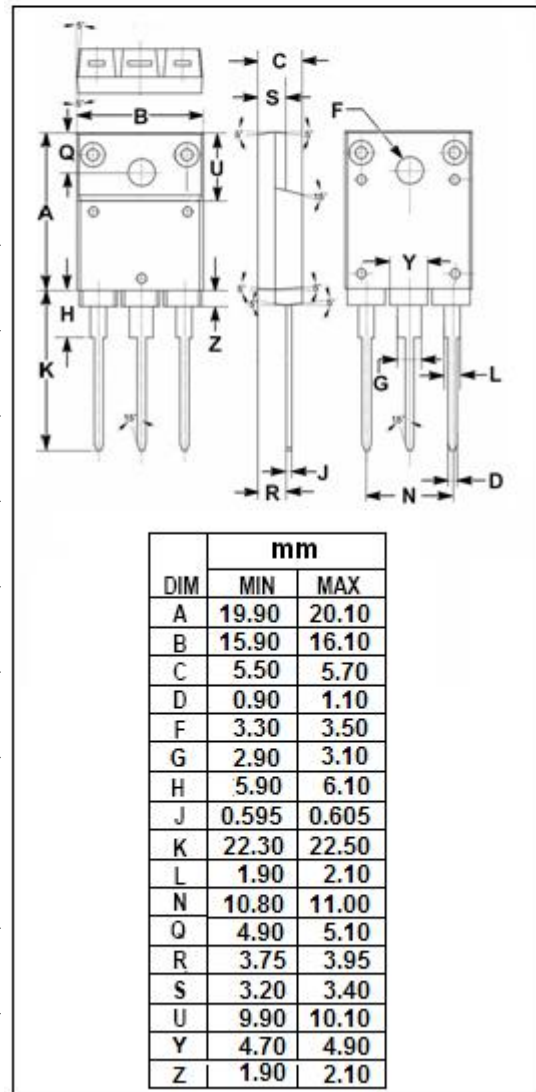
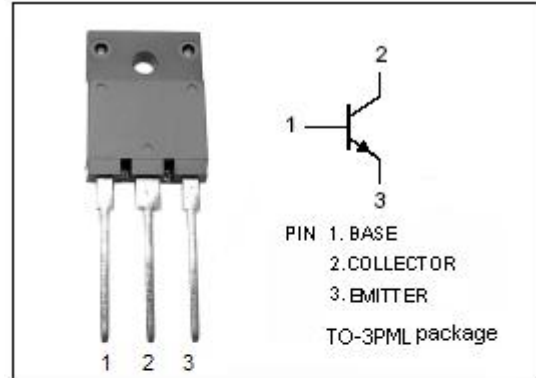
- High Breakdown Voltage-  
:  $V_{(BR)CBO} = 1700V(\text{Min})$
- High Switching Speed
- High Reliability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Ultrahigh-definition color display horizontal deflection output applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

| SYMBOL    | PARAMETER  | VALUE   | UNIT             |
|-----------|--|---------|------------------|
| $V_{CBO}$ | Collector-Base Voltage                               | 1700    | V                |
| $V_{CEO}$ | Collector-Emitter Voltage                            | 900     | V                |
| $V_{EBO}$ | Emitter-Base Voltage                                 | 6       | V                |
| $I_C$     | Collector Current-Continuous                         | 6       | A                |
| $I_{CP}$  | Collector Current-Peak                               | 16      | A                |
| $P_C$     | Collector Power Dissipation @ $T_a=25^\circ\text{C}$ | 2.5     | W                |
|           | Collector Power Dissipation @ $T_c=25^\circ\text{C}$ | 50      |                  |
| $T_J$     | Junction Temperature                                 | 150     | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature Range                            | -55~150 | $^\circ\text{C}$ |



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**ELECTRICAL CHARACTERISTICS**
 $T_C=25^{\circ}\text{C}$  unless otherwise specified

| SYMBOL         | PARAMETER                            | CONDITIONS                        | MIN | TYP. | MAX | UNIT |
|----------------|--------------------------------------|-----------------------------------|-----|------|-----|------|
| $V_{CEO(SUS)}$ | Collector-Emitter Sustaining Voltage | $I_C=0.1\text{A}; I_B=0$          | 900 |      |     | V    |
| $V_{CE(sat)}$  | Collector-Emitter Saturation Voltage | $I_C=5\text{A}; I_B=1\text{A}$    |     |      | 5.0 | V    |
| $V_{BE(sat)}$  | Base-Emitter Saturation Voltage      | $I_C=5\text{A}; I_B=1\text{A}$    |     |      | 1.5 | V    |
| $I_{CES}$      | Collector Cutoff Current             | $V_{CE}=1700\text{V}; R_{BE}=0$   |     |      | 0.5 | mA   |
| $I_{EBO}$      | Emitter Cutoff Current               | $V_{EB}=6\text{V}; I_C=0$         |     |      | 0.1 | mA   |
| $h_{FE-1}$     | DC current gain                      | $I_C=1\text{A}; V_{CE}=5\text{V}$ | 10  |      | 35  |      |

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